

SPTECH Silicon PNP Power Transistor

2SA1964

DESCRIPTION

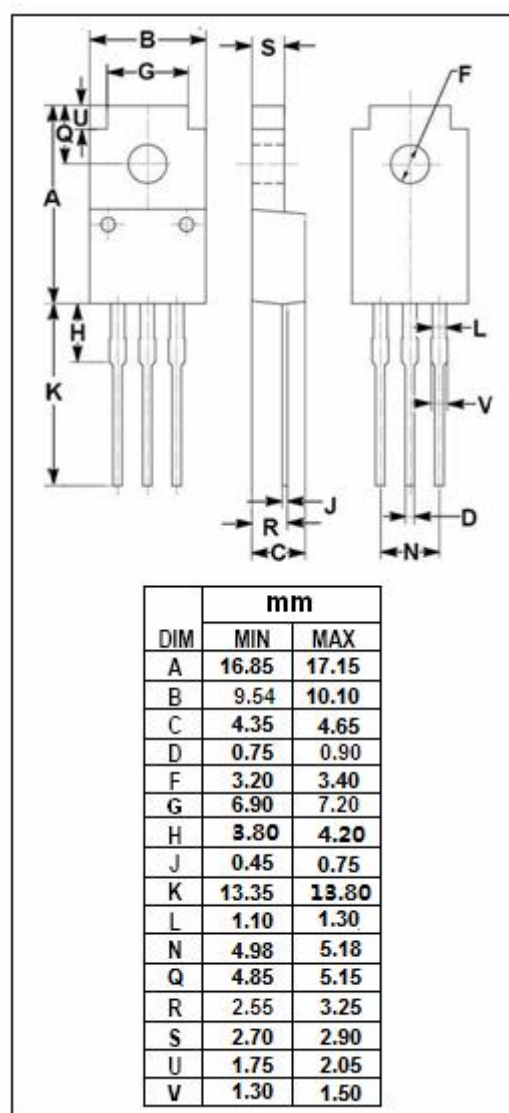
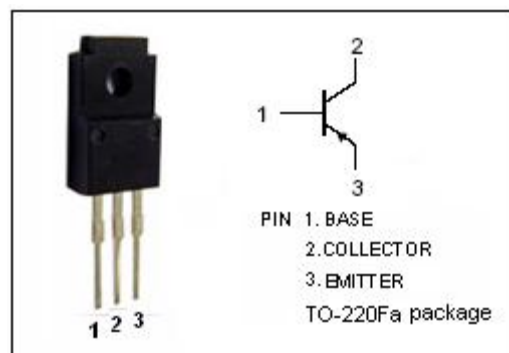
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -160V(\text{Min})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SC5248

APPLICATIONS

- Power amplifier applications.
- Driver stage amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-160	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	20	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; I _B = 0	-160			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -50 μA; I _E = 0	-160			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -50 μA; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1A; I _B = -0.1A			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -160V; I _E = 0			-1.0	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-1.0	μA
h _{FE}	DC Current Gain	I _C = -0.1A; V _{CE} = -5V	60		200	
f _T	Current-Gain—Bandwidth Product	I _C = -0.2A; V _{CE} = -10V		150		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		35		pF

◆ h_{FE} Classifications

D	E
60-120	100-200